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(54) **SEMICONDUCTOR DEVICE AND MANUFACTURE THEREOF**

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(57) Abstract:

PROBLEM TO BE SOLVED: To provide a semiconductor device for which a conductive layer constituting particles will not diffuse into an insulating layer, even if the width of the conductive layer is widened.

SOLUTION: This semiconductor device is provided with an insulating layer 2, a barrier layer 4, a conductive layer 5, a barrier layer 6 having an aperture part 11, and insulating layer 7 having a through-hole 8, with which the surface of the conductive layer 5 and a part of the surface of the barrier layer 6 are made to be exposed, a barrier layer 9 which is formed on the side face of the through-hole 8 and on the insulating layer 7 and comes into contact with the upper surface 6a of the barrier layer 6, and a conductive layer 10 with which the aperture part 11 and the through-hole 8 are filled. Since all the parts of the conductive layers 5 and 10 come in contact with the barrier layers 4, 6 and 9 in this semiconductor device, the copper contained in the conductive layers 5 and 10 will not diffuse into silicon dioxide which constitutes the insulating layers 2 and 7.

